Amended Claims

1. The use of compounds of the formula I

$R^1 [O (EO)_x (AO)_y H]_z$

where

R^1	is a z-valent alkyl radical having from 1 to 20 carbon atoms
(EO)	is an ethyleneoxy radical
(AO)	is an alkyleneoxy radical having from 3 to 10 carbon atoms
x	is a number from 3 to 12, in particular from 5 to 10
y	is a number from 0 to 10, in particular from 4 to 8
z	is a number from 1 to 6, in particular from 1 to 3,

for producing carrier fluids for abrasives, in particular cutting fluids, having a reduced water uptake for removal of material, in particular for sawing wafers by means of a wire saw, having a water content of less than 1% by weight.

2. The use according to claim 1, wherein, in the formula I,

R^1	is a z-valent alkyl radical having from 5 to 10 carbons, in particular pentyl.

3. The use according to at least one of the preceding claims, wherein the wafer is a semiconductor, in particular silicon.

4. The use according to at least one of the preceding claims, wherein the carrier fluid, in particular cutting fluid, is used in a slurry together with cutting grains, where metal, carbide, nitride, metal oxide, boride or diamond grains are used as cutting grains.

5. The use according to at least one of the preceding claims, wherein the carrier fluid, in particular cutting fluid, is worked up to separate off the resulting abraded material during or after removal of the material, in particular after cutting.

6. A carrier fluid, in particular cutting fluid, comprising at least one compound of the formula I

$R^1 [O (EO)_x (AO)_y H]_z$

where

R^1	is a z-valent alkyl radical having from 5 to 10 carbon atoms	
(EO)	is an ethyleneoxy radical	
(AO)	is an alkyleneoxy radical having from 3 to 10 carbon atoms	
x	is a number	from 3 to 12, in particular from 5 to 10
y	is a number	from 0.5 to 10, in particular from 4 to 8
z	is a number	from 1 to 6, in particular from 1 to 3, having a water content of less than 1% by weight.

7. The carrier fluid, in particular cutting fluid, according to claim 6 , wherein R^1 is pentyl.

8. The carrier fluid, in particular cutting fluid, according to claim 6, wherein the contact angle of the carrier fluid, in particular cutting fluid, on V2A steel at 25°C is from 25 to 50°.

9. The use of a carrier fluid, in particular cutting fluid, according to at least one of the preceding claims for the removal of material, in particular during sawing of wafers, from an object to be cut, in particular semiconductor, in particular silicon, by means of a saw using cutting grains, in particular silicon carbide grains.

10. The use of a carrier fluid according to at least one of the preceding claims for polishing materials, in particular for polishing wafers of silicon or of materials composed of polymers, in particular for lens production.

11. A method of cutting wafers from an object by means of a saw using a slurry composed of a cutting fluid and cutting grains, in particular cutting grains composed of metal, a carbide, nitride, oxide, boride, α-alumina or diamond, wherein the cutting fluid is a cutting fluid according to at least one of the preceding claims which is optionally worked up to separate off the resulting abraded material during or after removal of the material, in particular after cutting.

12. A method of polishing materials, in particular materials composed of silicon or polymers, using a slurry composed of a carrier fluid and abrasive materials, wherein a carrier fluid according to at least one of the preceding claims is used as carrier fluid.

13. A wafer, in particular silicon wafer, obtained according to at least one of the preceding claims.

14. A compound of the formula II

$$R^1\ O\ (EO)_x\ (AO)_y\ H$$

where

R^1	is 2-methylbutyl or 3-methylbutyl and
(EO), (AO), x and y	are as defined in claim 1.

THE CLAIMS DEFINING THE INVENTION ARE AS FOLLOWS:

1. The use of compounds of the formula I

$R^1 [O (EO)_x (AO)_y H]_z$

where

R^1 is a z-valent alkyl radical having from 1 to 20 carbon atoms

(EO) is an ethyleneoxy radical

(AO) is an alkyleneoxy radical having from 3 to 10 carbon atoms

x is a number from 3 to 12, in particular from 5 to 10

y is a number from 0 to 10, in particular from 4 to 8

z is a number from 1 to 6, in particular from 1 to 3,

for producing carrier fluids for abrasives, in particular cutting fluids, having a reduced water uptake for removal of material, in particular for sawing wafers by means of a wire saw, having a water content of less than 1% by weight.

2. The use according to claim 1, wherein, in the formula I,

R^1 is a z-valent alkyl radical having from 5 to 10 carbon atoms, in particular pentyl.

3. The use according to at least one of the preceding claims, wherein the wafer is a semiconductor, in particular silicon.

4. The use according to at least one of the preceding claims, wherein the carrier fluid, in particular cutting fluid, is used in a slurry together with cutting grains, where metal, carbide, nitride, metal oxide, boride or diamond grains are used as cutting grains.

5. The use according to at least one of the preceding claims, wherein the carrier fluid, in particular cutting fluid, is worked up to separate off the resulting abraded material during or after removal of the material, in particular after cutting,

6. A carrier fluid, in particular cutting fluid, comprising at least one compound of the formula I

$R^1 [O (EO)_x (AO)_y H]_z$

where

R^1 is a z-valent alkyl radical having from 5 to 10 carbon atoms

(EO) is an ethyleneoxy radical

(AO) is an alkyleneoxy radical having from 3 to 10 carbon atoms

x is a number from 3 to 12, in particular from 5 to 10

y is a number from 0.5 to 10, in particular from 4 to 8

z is a number from 1 to 6, in particular from 1 to 3, having a water content of less than 1% by weight.

7. The carrier fluid, in particular cutting fluid, according to claim 6, wherein R^1 is pentyl.

8. The carrier fluid, in particular cutting fluid, according to claim 6, wherein the contact angle of the carrier fluid, in particular cutting fluid, on V2A steel at 25°C is from 25 to 50°.

9. The use of a carrier fluid, in particular cutting fluid, according to at least one of the preceding claims for the removal of material, in particular during sawing of wafers, from an object to be cut, in particular semiconductor, in particular silicon, by means of a saw using cutting grains, in particular silicon carbide grains.

10. The use of a carrier fluid according to at least one of the preceding claims for polishing materials, in particular for polishing wafers of silicon or of materials composed of polymers, in particular for lens production.

11. A method of cutting wafers from an object by means of a saw using a slurry composed of a cutting fluid and cutting grains, in particular cutting grains composed of metal, a carbide, nitride, oxide, boride, α-alumina or diamond, wherein the cutting fluid is a cutting fluid according to at least one of the preceding claims which is optionally worked up to separate off the resulting abraded material during or after removal of the material, in particular after cutting.

12. A method of polishing materials, in particular materials composed of silicon or polymers, using a slurry composed of a carrier fluid and abrasive materials, wherein a carrier fluid according to at least one of the preceding claims is used as carrier fluid.

13. A wafer, in particular silicon wafer, obtained according to at least one of the preceding claims.

14. A compound of the formula II

$$R^1\ O\ (EO)_x\ (AO)_y\ H$$

where

R^1	is 2-methylbutyl or 3-methylbutyl and
(EO), (AO), x and y	are as defined in claim 1.